

NTHD4102P

Power MOSFET

–20 V, –4.1 A, Dual P–Channel ChipFET™

Features

- Offers an Ultra Low $R_{DS(ON)}$ Solution in the ChipFET Package
- Miniature ChipFET Package 40% Smaller Footprint than TSOP–6
- Low Profile (<1.1 mm) Allows it to Fit Easily into Extremely Thin Environments such as Portable Electronics
- Simplifies Circuit Design since Additional Boost Circuits for Gate Voltages are not Required
- Operated at Standard Logic Level Gate Drive, Facilitating Future Migration to Lower Levels using the same Basic Topology
- Pb–Free Package is Available

Applications

- Optimized for Battery and Load Management Applications in Portable Equipment such as MP3 Players, Cell Phones, and PDAs
- Charge Control in Battery Chargers
- Buck and Boost Converters

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain–to–Source Voltage			V_{DSS}	–20	V
Gate–to–Source Voltage			V_{GS}	± 8.0	V
Continuous Drain Current (Note 1)	Steady State	$T_{\text{A}} = 25^{\circ}\text{C}$	I_{D}	–2.9	A
		$T_{\text{A}} = 85^{\circ}\text{C}$		–2.1	
	$t \leq 10\text{ s}$	$T_{\text{A}} = 25^{\circ}\text{C}$		–4.1	
Power Dissipation (Note 1)	Steady State	$T_{\text{A}} = 25^{\circ}\text{C}$	P_{D}	1.1	W
	$t \leq 10\text{ s}$			2.1	
Pulsed Drain Current	$t_{\text{p}} = 10\text{ ms}$		I_{DM}	–13.8	A
Operating Junction and Storage Temperature			$T_{\text{J}}, T_{\text{STG}}$	–55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode)			I_{S}	–1.1	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_{L}	260	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction–to–Ambient, Steady State (Note 1)	$R_{\theta JA}$	113	$^\circ\text{C/W}$
Junction–to–Ambient, $t \leq 10\text{ s}$ (Note 1)		60	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

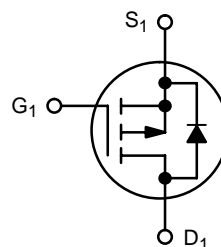
1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)



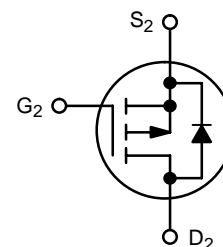
ON Semiconductor®

<http://onsemi.com>

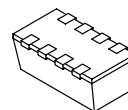
$V_{(BR)DSS}$	$R_{DS(ON)}$ TYP	I_D MAX
–20 V	64 m Ω @ –4.5 V	–4.1 A
	85 m Ω @ –2.5 V	
	120 m Ω @ –1.8 V	



P–Channel MOSFET

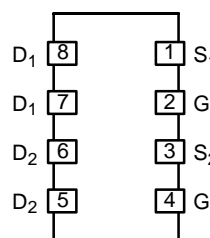


P–Channel MOSFET

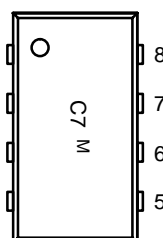


ChipFET
CASE 1206A
STYLE 2

PIN CONNECTIONS



MARKING DIAGRAM



C7 = Specific Device Code
M = Month Code

ORDERING INFORMATION

Device	Package	Shipping†
NTHD4102PT1	ChipFET	3000/Tape & Reel
NTHD4102PT1G	ChipFET (Pb–Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTHD4102P

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(Br)DSS}	V _{GS} = 0 V, I _D = -250 μA	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(Br)DSS} /T _J			-15		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V V _{DS} = -16 V			-1.0	μA
		T _J = 25°C T _J = 85°C			-5.0	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8.0 V			±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250 μA	-0.45		-1.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			2.7		mV/°C
Drain-to-Source On Resistance	R _{DS(ON)}	V _{GS} = -4.5 V, I _D = -2.9 A		64	80	mΩ
		V _{GS} = -2.5 V, I _D = -2.2 A		85	110	
		V _{DS} = -1.8 V, I _D = -1.0 A		120	170	
Forward Transconductance	g _{FS}	V _{DS} = -10 V, I _D = -2.9 A		7.0		S

CHARGES, CAPACITANCES, AND GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = -16 V		750		pF
Output Capacitance	C _{OSS}			100		
Reverse Transfer Capacitance	C _{RSS}			45		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = -4.5 V, V _{DS} = -16 V, I _D = -2.6 A		7.6	8.6	nC
Gate-to-Source Charge	Q _{GS}			1.3		
Gate-to-Drain Charge	Q _{GD}			2.6		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = -4.5 V, V _{DD} = -16 V, I _D = -2.6 A, R _G = 2.0 Ω		5.5	10	ns
Rise Time	t _r			12	25	
Turn-Off Delay Time	t _{d(OFF)}			32	40	
Fall Time	t _f			23	35	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -1.1 A		-0.8	-1.2	V
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 1.0 A		20	40	ns
Charge Time	t _a			15		
Discharge Time	t _b			5		
Reverse Recovery Charge	Q _{RR}			0.01		

- Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2%
- Switching characteristics are independent of operating junction temperatures

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

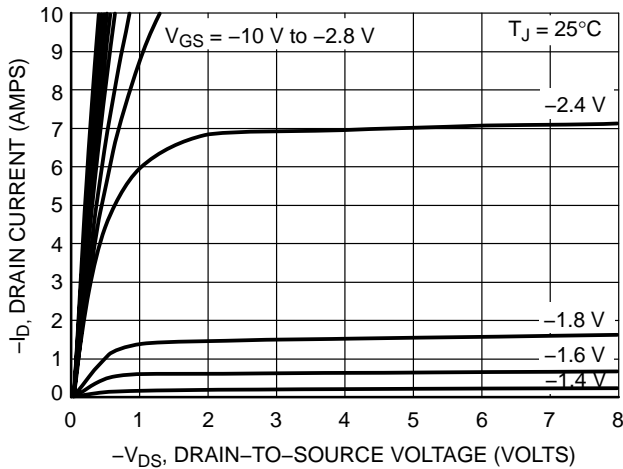


Figure 1. On-Region Characteristics

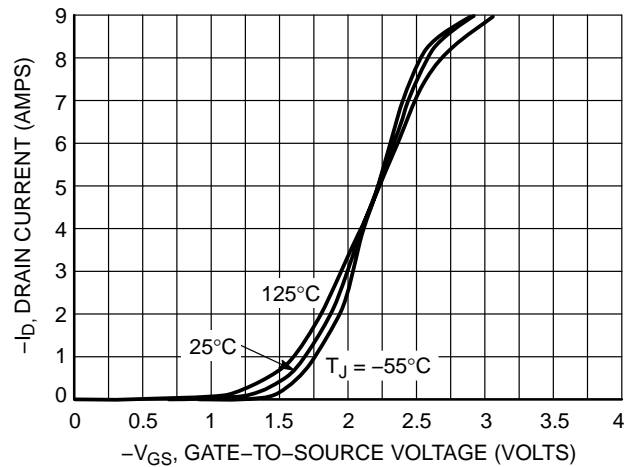


Figure 2. Transfer Characteristics

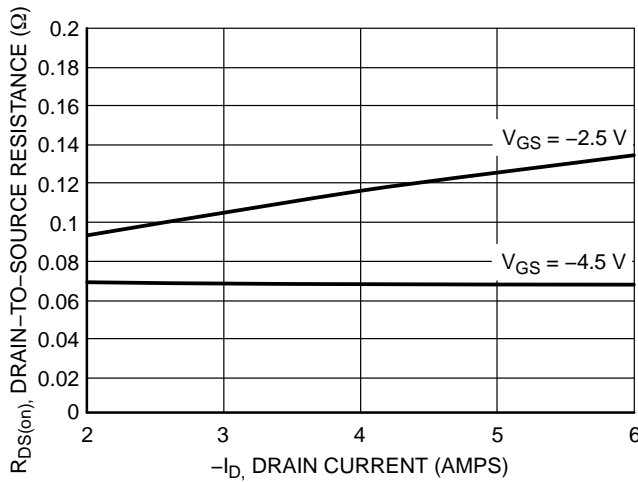


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

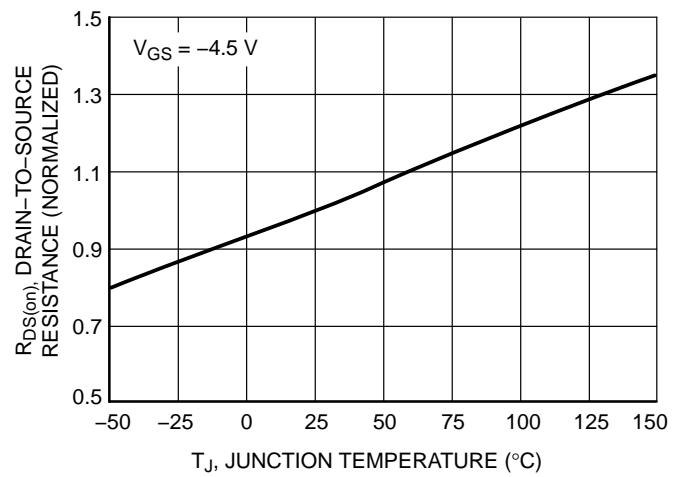


Figure 4. On-Resistance Variation with Temperature

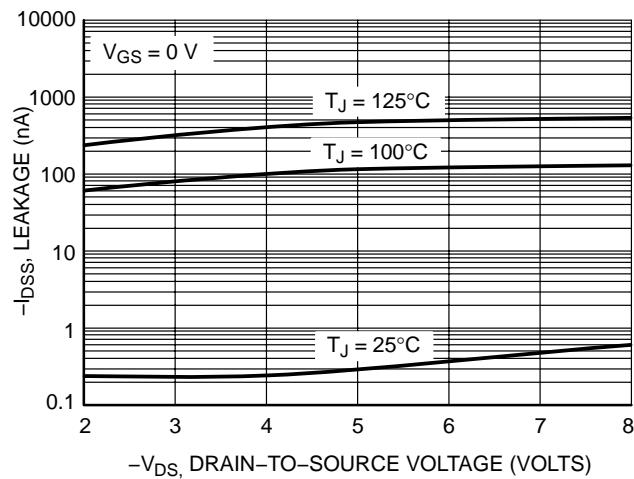
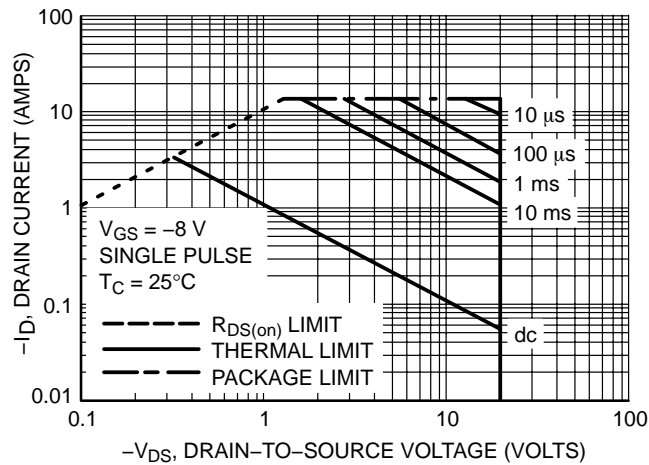
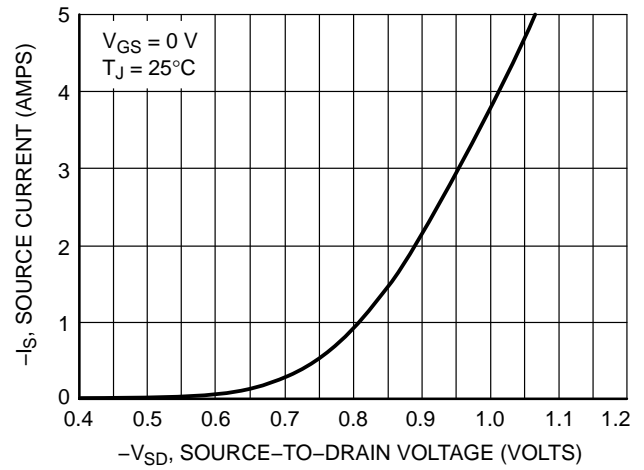
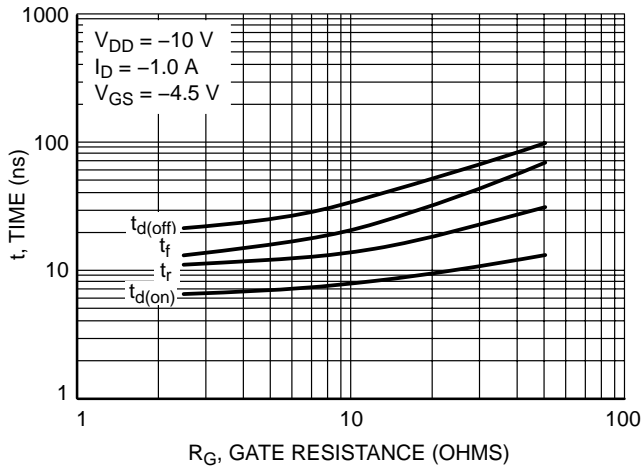
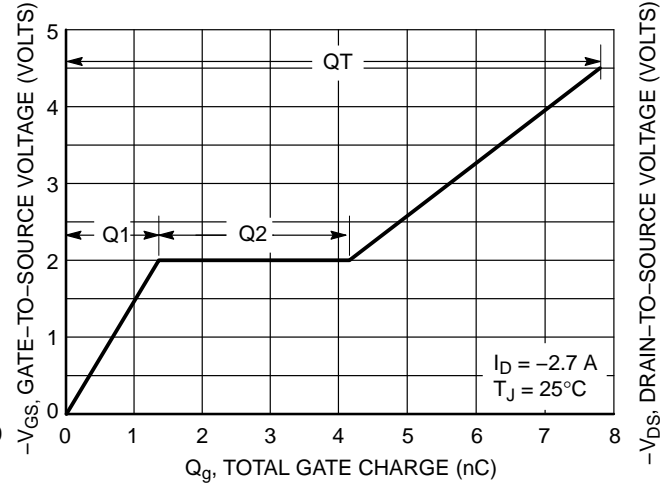
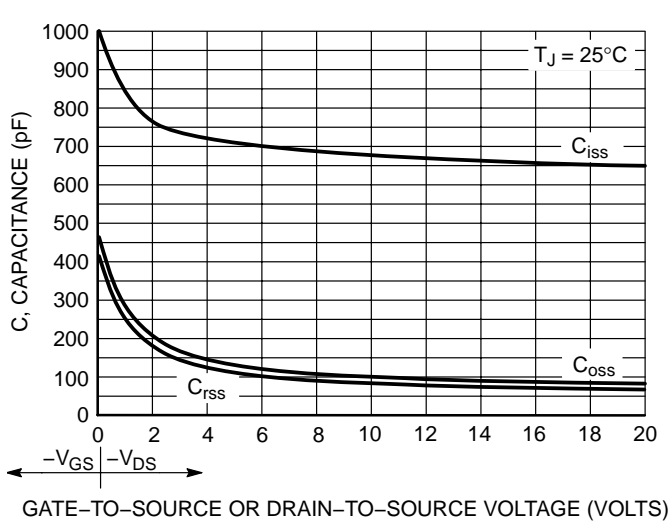


Figure 5. Drain-to-Source Leakage Current vs. Voltage

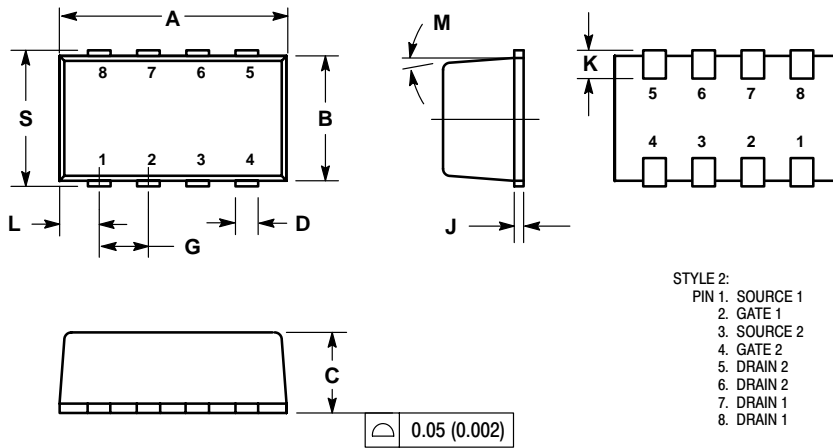
TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)



NTHD4102P

PACKAGE DIMENSIONS

ChipFET™
CASE 1206A-03
ISSUE E

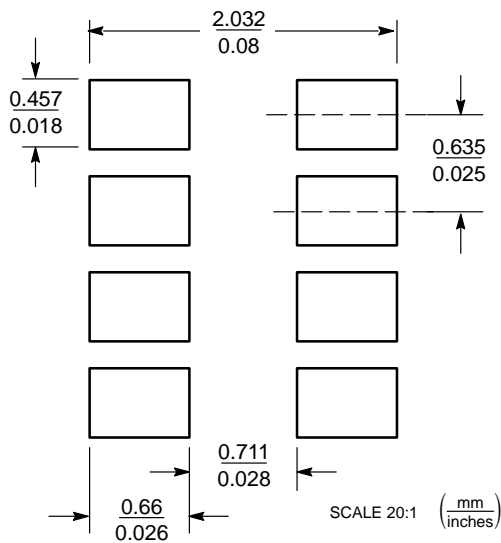


NOTES:

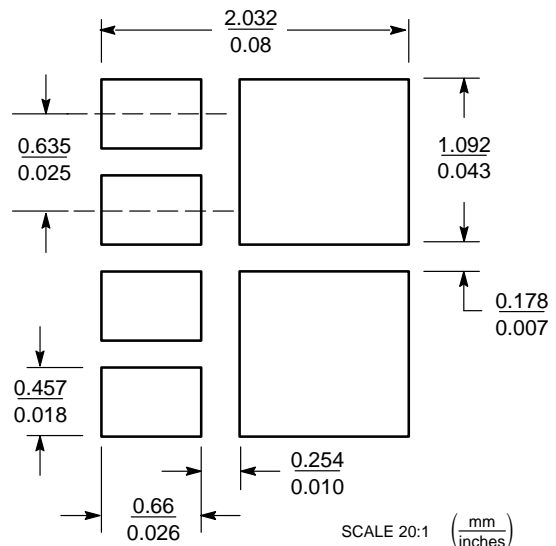
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.
7. 1206A-01 AND 1206A-02 OBSOLETE. NEW STANDARD IS 1206A-03.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.95	3.10	0.116	0.122
B	1.55	1.70	0.061	0.067
C	1.00	1.10	0.039	0.043
D	0.25	0.35	0.010	0.014
G	0.65 BSC		0.025 BSC	
J	0.10	0.20	0.004	0.008
K	0.28	0.42	0.011	0.017
L	0.55 BSC		0.022 BSC	
M	5° NOM		5° NOM	
S	1.80	2.00	0.072	0.080

SOLDERING FOOTPRINT*




Basic



Style 2

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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